

Negative photoconductivity of InAs nanowire

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Supporting Information

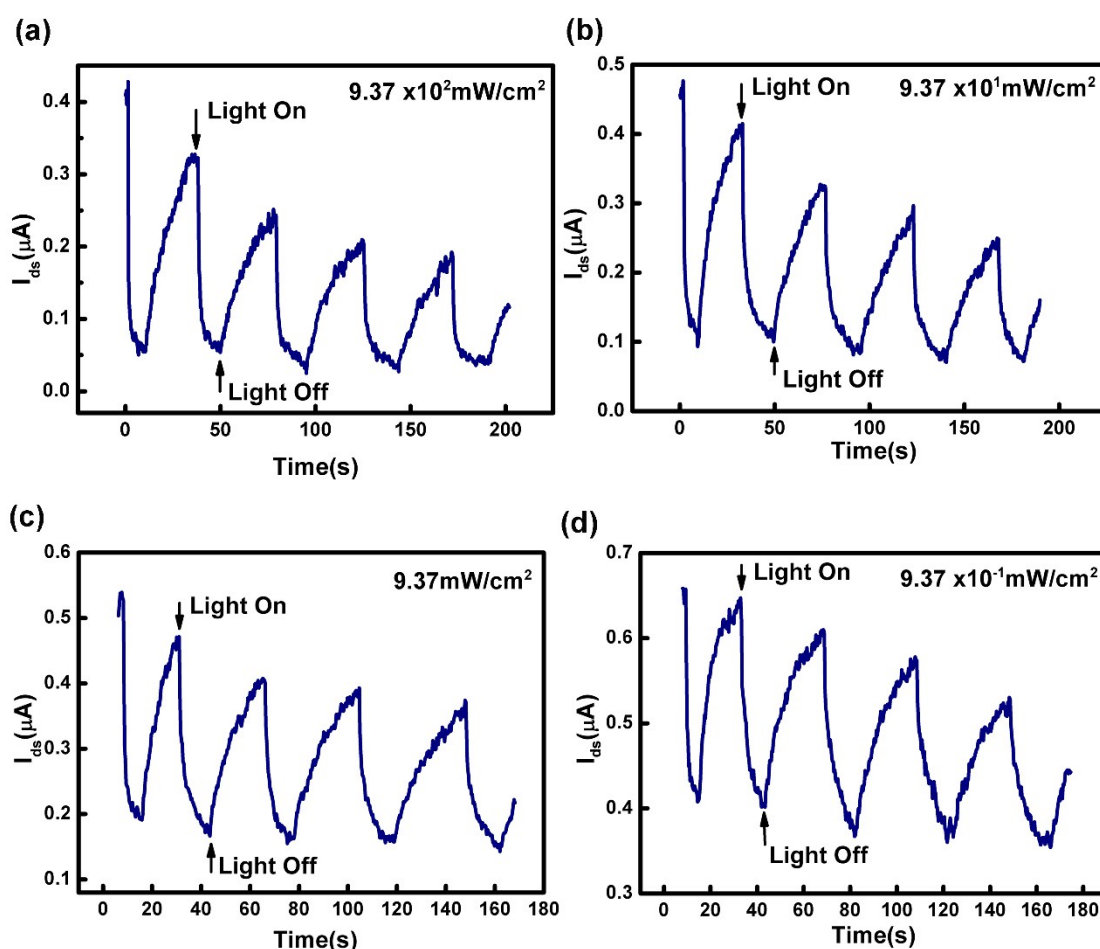


Figure S1. Time-resolved photocurrent rise and decay curves as obtained by application and removal of 633nm light illumination at $V_{ds}=0.1$ V, $V_{gs}=20$ V under different light intensity varying from $9.37 \times 10^{-1} \text{ mW}\cdot\text{cm}^{-2}$ to $9.37 \times 10^3 \text{ mW}\cdot\text{cm}^{-2}$.

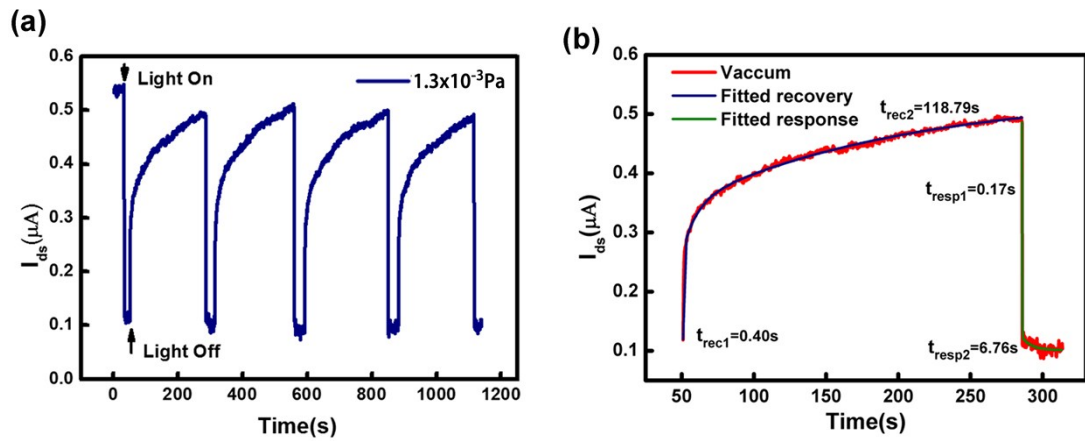


Figure S2. Photoelectrical response properties of InAs NW under 405 nm, 9.37×10^3 $\text{mW}\cdot\text{cm}^{-2}$ light illumination at $V_{\text{ds}}=0.1$ V, $V_{\text{gs}}=30$ V in 1.3×10^{-3} Pa vacuum and (b) shows the fitting curve.

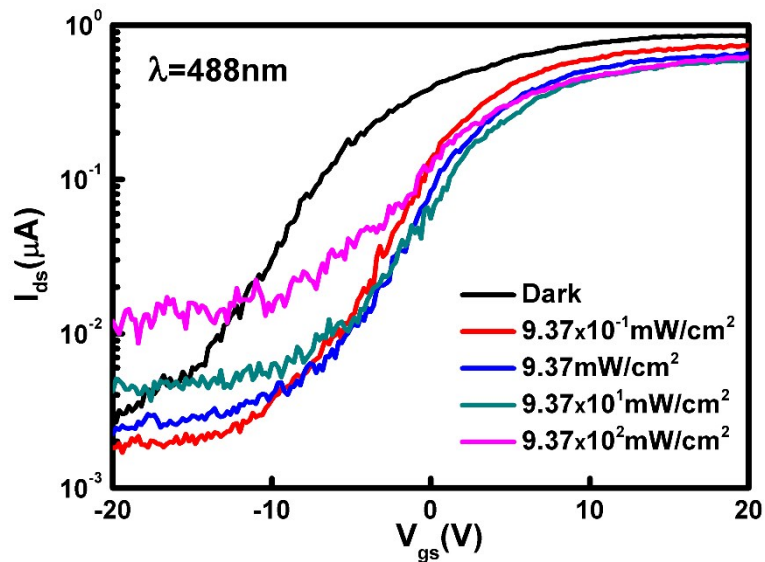


Figure S3. Logarithmic form of the $I_{\text{d}}-V_{\text{g}}$ curves of the InAs NW FET under 488 nm light illumination.